## IN THE CLAIMS:

1. (Previously Presented) A semiconductor device comprising:

a semiconductor layer having a crystalline structure on an insulating surface, the semiconductor layer having at least a source region, a drain region and a channel region,

wherein the channel region contains a rare gas element having a concentration gradient, and the channel region has at least a first portion and a second portion, the second portion being more distant from the insulating surface than the first portion, and

wherein a crystallinity of the first portion in the channel region is higher than that of the second portion in the channel region.

- 2. (Canceled)
- 3. (Original) A semiconductor device according to claim 1, wherein the semiconductor device is a liquid crystal display device.
- 4. (Original) A semiconductor device according to claim 1, wherein the semiconductor device is an EL display device.
- 5. (Original) A semiconductor device according to claim 1, wherein the semiconductor device is at least one selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle type display, a player using a recording medium, a digital camera, a projector, a portable telephone, and a portable book.
  - 6. (Currently Amended) A semiconductor device comprising:
- a semiconductor layer having a crystalline structure on an insulating surface, the semiconductor layer having at least a source region, a drain region and a channel region, an insulating film on the semiconductor layer,

wherein a rare gas element having a concentration gradient is contained between the channel region and the insulating film, and the channel region has at least a first portion and a second portion, the second portion contains a rare gas element having a concentration

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gradient, the second portion being more distant from the insulating surface than the first portion, and

wherein a crystallinity of the first portion in the channel region is higher than that of the second portion in the channel region.

- 7. (Canceled)
- 8. (Original) A semiconductor device according to claim 6, wherein the semiconductor device is a liquid crystal display device.
- 9. (Original) A semiconductor device according to claim 6, wherein the semiconductor device is an EL display device.
- 10. (Original) A semiconductor device according to claim 6, wherein the semiconductor device is at least one selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle type display, a player using a recording medium, a digital camera, a projector, a portable telephone, and a portable book.
  - 11. (Currently Amended) A semiconductor device comprising:
  - a first semiconductor layer having a crystalline structure on an insulating surface;
  - a second semiconductor layer on the first semiconductor layer;
  - a channel region in the first semiconductor layer and the second semiconductor layer;
  - an insulating film in contact with the second semiconductor layer; and
  - an electrode in contact with the insulating film,

wherein the channel region in the second semiconductor layer contains a rare gas element having a concentration gradient, and

wherein a crystallinity of the channel region in the first semiconductor layer is higher than that of the channel region in the second semiconductor layer.

- 12. (Original) A semiconductor device according to claim 11, wherein the second semiconductor layer has a crystalline structure.
- 13. (Original) A semiconductor device according to claim 11, wherein the second semiconductor layer has an amorphous structure.
  - 14. (Canceled)
- 15. (Original) A semiconductor device according to claim 11, wherein the semiconductor device is a liquid crystal display device.
- 16. (Original) A semiconductor device according to claim 11, wherein the semiconductor device is an EL display device.
- 17. (Original) A semiconductor device according to claim 11, wherein the semiconductor device is at least one selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle type display, a player using a recording medium, a digital camera, a projector, a portable telephone, and a portable book.
  - 18. (Currently Amended) A semiconductor device comprising:
- a semiconductor layer having a crystalline structure on an insulating surface, the <u>semiconductor layer having at least a source region, a drain region and a channel region;</u>
  - a gate insulating film adjacent to the semiconductor layer,

wherein the semiconductor layer contains a rare gas element having a concentration gradient along a direction perpendicular to the insulating surface, and the channel region has at least a first portion and a second portion, the second portion being more distant from the insulating surface than the first portion, and

wherein a crystallinity of the first portion in the semiconductor layer is higher than that of the second portion in the semiconductor layer.

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19. (Canceled)

- 20. (Original) A semiconductor device according to claim 18, wherein the semiconductor device is a liquid crystal display device.
- 21 (Original) A semiconductor device according to claim 18, wherein the semiconductor device is an EL display device.
- 22. (Original) A semiconductor device according to claim 18, wherein the semiconductor device is at least one selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle type display, a player using a recording medium, a digital camera, a projector, a portable telephone, and a portable book.
- 23. (Currently Amended) A semiconductor device comprising: a semiconductor layer having a crystalline structure on an insulating surface, the semiconductor layer having at least a source region, a drain region and a channel region; a gate insulating film adjacent to the semiconductor layer, wherein the channel region has at least a first portion and a second portion. wherein the semiconductor layer contains a rare gas element, a first portion of the semiconductor layer having the first portion has a higher concentration of the rare gas element than a-second portion of the semiconductor layer the second portion,

wherein the first portion is closer to the gate insulating film than the second portion, and

wherein a crystallinity of the second portion is higher than that of the first portion.

- 24. (Canceled)
- 25. (Original) A semiconductor device according to claim 23, wherein the semiconductor device is a liquid crystal display device.

- 26. (Original) A semiconductor device according to claim 23, wherein the semiconductor device is an EL display device.
- 27. (Original) A semiconductor device according to claim 23, wherein the semiconductor device is at least one selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle type display, a player using a recording medium, a digital camera, a projector, a portable telephone, and a portable book.

28-40. (Canceled)

- 41. (Previously Presented) A semiconductor device according to claim 1, wherein the lower layer in the channel region comprises poly-silicon and the upper layer in the channel region comprises amorphous silicon.
- 42. (Previously Presented) A semiconductor device according to claim 6, wherein the lower layer in the channel region comprises poly-silicon and the upper layer in the channel region comprises amorphous silicon.
- 43. (Previously Presented) A semiconductor device according to claim 11, wherein the first semiconductor layer comprises poly-silicon and the second semiconductor layer comprises amorphous silicon.
- 44. (Previously Presented) A semiconductor device according to claim 18, wherein the lower layer in the channel region comprises poly-silicon and the upper layer in the channel region comprises amorphous silicon.
  - 45. (Currently Amended) A semiconductor device comprising: an electrode over an insulating surface; an insulating film over the electrode;

a semiconductor layer having at least a source region, a drain region and a channel region over the electrode with the insulating film interposed therebetween,

wherein the channel region contains a rare gas element having a concentration gradient,

wherein the channel region has at least a first portion and a second portion.

wherein the second portion is more distant from the insulating film than the first portion, and

wherein a crystallinity of the first portion in the channel region is higher than that of the second portion in the channel region.

- 46. (Previously Presented) A semiconductor device according to claim 45, wherein the semiconductor device is a liquid crystal display device.
- 47. (Previously Presented) A semiconductor device according to claim 45, wherein the semiconductor device is an EL display device.
- 48. (Previously Presented) A semiconductor device according to claim 45, wherein the semiconductor device is at least one selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle type display, a player using a recording medium, a digital camera, a projector, a portable telephone, and a portable book.
  - 49. (Currently Amended) A semiconductor device comprising:

an electrode over an insulating surface;

an insulating film over the electrode;

a semiconductor layer having at least a source region, a drain region and a channel region over the electrode with the insulating film interposed therebetween.

wherein the channel region has at least a first portion and a second portion,
wherein a rare gas element having a concentration gradient is contained in the
semiconductor layer the second portion contains a rare gas element having a concentration
gradient,

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wherein the second portion is more distant from the insulating film than the first portion, and

wherein a crystallinity of the first portion in the channel region is higher than that of the second portion in the channel region.

- 50. (Previously Presented) A semiconductor device according to claim 49, wherein the semiconductor device is a liquid crystal display device.
- 51. (Previously Presented) A semiconductor device according to claim 49, wherein the semiconductor device is an EL display device.
- 52. (Previously Presented) A semiconductor device according to claim 49, wherein the semiconductor device is at least one selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle type display, a player using a recording medium, a digital camera, a projector, a portable telephone, and a portable book.
  - 53. (Currently Amended) A semiconductor device comprising:
  - an electrode over an insulating surface;
  - an insulating film over the electrode;
- a first semiconductor layer over the electrode with the insulating film interposed therebetween; [[and]]
  - a second semiconductor layer over the first semiconductor layer[[,]]; and
  - a channel region in the first semiconductor layer and the second semiconductor layer,
- wherein the channel region in the second semiconductor layer contains a rare gas element having a concentration gradient, and

wherein a crystallinity of the channel region in the first semiconductor layer is higher than that of the channel region in the second semiconductor layer.

54. (Previously Presented) A semiconductor device according to claim 53, wherein the semiconductor device is a liquid crystal display device.

- 55. (Previously Presented) A semiconductor device according to claim 53, wherein the semiconductor device is an EL display device.
- 56. (Previously Presented) A semiconductor device according to claim 53, wherein the semiconductor device is at least one selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle type display, a player using a recording medium, a digital camera, a projector, a portable telephone, and a portable book.